

IN THE CLAIMS:

Listing of claims:

1-16. (canceled)

17. (currently amended) A method of manufacturing a semiconductor device
~~according to claim 4, further comprising:~~
forming an insulating layer above a semiconductor substrate;
forming a conducting region above the insulating layer, the conducting region selected
from the group consisting of a gate electrode and an undercoat wiring;
forming a dielectric layer above the conducting region;
forming a film comprising a titanium nitride layer containing oxygen atoms within a
range of from 5 to 25 atomic %;
forming an electrode for a capacitive element above the dielectric layer by processing the
film;
forming an out-going electrode connected to the electrode for the capacitive element; and
forming at least one of a resistance element and a fuse element, wherein the electrode for
the capacitive element has the same composition as that of the at least one of a resistance
element and a fuse element.

18. (currently amended) A method of manufacturing a semiconductor device
~~according to claim 4, further comprising:~~
forming an insulating layer above a semiconductor substrate;
forming a conducting region above the insulating layer, the conducting region selected
from the group consisting of a gate electrode and an undercoat wiring;
forming a dielectric layer above the conducting region;
forming a film comprising a titanium nitride layer containing oxygen atoms within a
range of from 5 to 25 atomic %;

_____ forming an electrode for a capacitive element above the dielectric layer by processing the film;

_____ forming an out-going electrode connected to the electrode for the capacitive element; and

_____ forming the electrode for the capacitive element simultaneously with the one of a resistance element and a fuse element.

19-20. (canceled)